

2SC5552

Silicon NPN triple diffusion mesa type

For horizontal deflection output

■ Features

- High breakdown voltage, and high reliability through the use of a glass passivation layer
- High-speed switching
- Wide safe operation area

■ Absolute Maximum Ratings $T_C = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V_{CBO}	1 700	V
Collector-emitter voltage (E-B short)	V_{CES}	1 700	V
Collector-emitter voltage (Base open)	V_{CEO}	600	V
Emitter-base voltage (Collector open)	V_{EBO}	7	V
Base current	I_B	8	A
Collector current	I_C	16	A
Peak collector current *	I_{CP}	30	A
Collector power dissipation	P_C	65	W
		$T_a = 25^\circ\text{C}$	
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

Note) *: Non-repetitive peak collector current

■ Electrical Characteristics $T_C = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = 1\ 000\ \text{V}, I_E = 0$			50	μA
		$V_{CB} = 1\ 700\ \text{V}, I_E = 0$			1	mA
Emitter-base cutoff current (Collector open)	I_{EBO}	$V_{EB} = 7\ \text{V}, I_C = 0$			50	μA
Forward current transfer ratio	h_{FE}	$V_{CE} = 5\ \text{V}, I_C = 8\ \text{A}$	6		12	—
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 8\ \text{A}, I_B = 2\ \text{A}$			3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = 8\ \text{A}, I_B = 2\ \text{A}$			1.5	V
Transition frequency	f_T	$V_{CE} = 10\ \text{V}, I_C = 0.1\ \text{A}, f = 0.5\ \text{MHz}$		3		MHz
Storage time	t_{stg}	$I_C = 8\ \text{A}, \text{Resistance loaded}$			3.0	μs
Fall time	t_f	$I_{B1} = 2\ \text{A}, I_{B2} = -4\ \text{A}$			0.2	μs

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

